

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	9627	((257/698,752,758,773-776,781,786) or (257/E23.02,E23.152,E23.194)).CCLS.	USPAT	2008/07/03 11:46
2	IS&R	7215	((257/698,752,758,773-776,781,786) or (257/E23.02,E23.152,E23.194)).CCLS.	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2008/07/03 12:38
3	IS&R	7378	(438/612,614,618,622,629,637,639,640,666,668,672).CCLS.	USPAT	2008/07/03 13:01
4	IS&R	7201	(438/612,614,618,622,629,637,639,640,666,668,672).CCLS.	US-POPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2008/07/03 13:01
5	BRS	6343	S56 not S54	USPAT	2008/07/03 13:02
6	BRS	6248	S57 not S55	US-POPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2008/07/03 13:06
7	BRS	152	(active transistor gate) and ((bond bonding) near2 (pad)) and ((mesh meshed) near3 (wire wiring interconnect interconnection layer film))	USPAT	2008/07/03 16:58
8	BRS	135	(active transistor gate) and ((bond bonding) near2 (pad)) and ((mesh meshed) near3 (wire wiring interconnect interconnection layer film))	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2008/07/03 16:58

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L2	9	((active transistor gate) and ((bond bonding) near2 (pad)) and ((mesh meshed) near3 (wire wiring interconnect interconnection layer film))).clm.	US-PGPUB	2008/07/04 16:51